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Introduction

Artix™-7 FPGAs are available in -3, -2, -1, and -2L speed grades, with -3 having the highest performance. The -2L devices can operate at either of two V_{CCINT} voltages, 0.9V and 1.0V and are screened for lower maximum static power. When operated at $V_{CCINT} = 1.0V$, the speed specification of a -2L device is the same as the -2 speed grade. When operated at $V_{CCINT} = 0.9V$, the -2L static and dynamic power is reduced.

Artix-7 FPGA DC and AC characteristics are specified in commercial, extended, and industrial temperature ranges. Except the operating temperature range or unless otherwise noted, all the DC and AC electrical parameters are the same for a particular speed grade (that is, the timing

characteristics of a -1 speed grade industrial device are the same as for a -1 speed grade commercial device). However, only selected speed grades and/or devices are available in each temperature range.

All supply voltage and junction temperature specifications are representative of worst-case conditions. The parameters included are common to popular designs and typical applications.

This Artix-7 FPGA data sheet, part of an overall set of documentation on the 7 series FPGAs, is available on the Xilinx website at www.xilinx.com/7.

All specifications are subject to change without notice.

DC Characteristics

Table 1: Absolute Maximum Ratings⁽¹⁾

Symbol	Description	Min	Max	Units
FPGA Logic				
V_{CCINT}	Internal supply voltage	-0.5	1.1	V
V_{CCAUX}	Auxiliary supply voltage	-0.5	2.0	V
V_{CCBRAM}	Supply voltage for the block RAM memories	-0.5	1.1	V
V_{CCO}	Output drivers supply voltage for 3.3V HR I/O banks	-0.5	3.6	V
V_{REF}	Input reference voltage	-0.5	2.0	V
$V_{IN}^{(2)(3)(4)(5)}$	I/O input voltage	-0.5	$V_{CCO} + 0.5$	V
	I/O input voltage for V_{REF} and differential I/O standards	-0.5	2.625	V
V_{CCBATT}	Key memory battery backup supply	-0.5	2.0	V
GTP Transceiver				
$V_{MGTAVCC}$	Analog supply voltage for the GTP transmitter and receiver circuits	-0.5	1.1	V
$V_{MGTAVTT}$	Analog supply voltage for the GTP transmitter and receiver termination circuits	-0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	-0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	-0.5	1.26	V
I_{DCIN}	DC input current for receiver input pins DC coupled $V_{MGTAVTT} = 1.2V$	-	10	mA
I_{DCOUT}	DC output current for transmitter pins DC coupled $V_{MGTAVTT} = 1.2V$	-	10	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	-0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	-0.5	2.0	V

Table 1: Absolute Maximum Ratings⁽¹⁾ (Cont'd)

Symbol	Description	Min	Max	Units
Temperature				
T _{STG}	Storage temperature (ambient)	-65	150	°C
T _{SOL}	Maximum soldering temperature for Pb/Sn component bodies ⁽⁶⁾	-	+220	°C
	Maximum soldering temperature for Pb-free component bodies ⁽⁶⁾	-	+260	°C
T _j	Maximum junction temperature ⁽⁶⁾	-	+125	°C

Notes:

- Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
- The lower absolute voltage specification always applies.
- For I/O operation, refer to [UG471: 7 Series FPGAs SelectIO Resources User Guide](#).
- The maximum limit applied to DC signals.
- For maximum undershoot and overshoot AC specifications, see [Table 4](#).
- For soldering guidelines and thermal considerations, see [UG475: 7 Series FPGA Packaging and Pinout Specification](#).

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾

Symbol	Description	Min	Typ	Max	Units
FPGA Logic					
V _{CCINT}	Internal supply voltage	0.95	1.00	1.05	V
	For -2L (0.9V) devices: internal supply voltage	0.87	0.90	0.93	V
V _{CCAUX}	Auxiliary supply voltage	1.71	1.80	1.89	V
V _{CCBRAM}	Block RAM supply voltage	0.95	1.00	1.05	V
V _{CCO} ⁽³⁾⁽⁴⁾	Supply voltage for 3.3V HR I/O banks	1.14	-	3.465	V
V _{IN} ⁽⁵⁾	I/O input voltage	-0.20	-	V _{CCO} + 0.20	V
	I/O input voltage for V _{REF} and differential I/O standards	-0.20	-	2.625	V
I _{IN} ⁽⁶⁾	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	-	-	10	mA
V _{CCBATT} ⁽⁷⁾	Battery voltage	1.0	-	1.89	V
GTP Transceiver					
V _{MGTAVCC} ⁽⁸⁾⁽⁹⁾	Analog supply voltage for the GTP transmitter and receiver circuits	0.97	1.0	1.03	V
V _{MGTAVTT} ⁽⁸⁾⁽⁹⁾	Analog supply voltage for the GTP transmitter and receiver termination circuits	1.17	1.2	1.23	V
XADC					
V _{CCADC}	XADC supply relative to GNDADC	1.71	1.80	1.89	V
V _{REFP}	Externally supplied reference voltage	1.20	1.25	1.30	V

Table 2: Recommended Operating Conditions⁽¹⁾⁽²⁾ (Cont'd)

Symbol	Description	Min	Typ	Max	Units
Temperature					
T_j	Junction temperature operating range for commercial (C) temperature devices	0	—	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	—	100	°C
	Junction temperature operating range for industrial (I) temperature devices	-40	—	100	°C

Notes:

1. All voltages are relative to ground.
2. For the design of the power distribution system consult [UG483, 7 Series FPGAs PCB Design and Pin Planning Guide](#).
3. Configuration data is retained even if V_{CCO} drops to 0V.
4. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, 2.5V, and 3.3V.
5. The lower absolute voltage specification always applies.
6. A total of 200 mA per bank should not be exceeded.
7. V_{CCBATT} is required only when using bitstream encryption. If battery is not used, connect V_{CCBATT} to either ground or V_{CCAUX} .
8. Each voltage listed requires the filter circuit described in [UG482: 7 Series FPGAs GTP Transceiver User Guide](#).
9. Voltages are specified for the temperature range of $T_j = 0^\circ\text{C}$ to $+85^\circ\text{C}$.

Table 3: DC Characteristics Over Recommended Operating Conditions

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	—	—	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	1.5	—	—	V
I_{REF}	V_{REF} leakage current per pin	—	—	15	μA
I_L	Input or output leakage current per pin (sample-tested)	—	—	15	μA
$C_{IN}^{(2)}$	Die input capacitance at the pad	—	—	8	pF
I_{RPU}	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 3.3\text{V}$	90	—	330	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 2.5\text{V}$	68	—	250	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.8\text{V}$	34	—	220	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.5\text{V}$	23	—	150	μA
	Pad pull-up (when selected) @ $V_{IN} = 0\text{V}$, $V_{CCO} = 1.2\text{V}$	12	—	120	μA
I_{RPD}	Pad pull-down (when selected) @ $V_{IN} = 3.3\text{V}$	68	—	330	μA
	Pad pull-down (when selected) @ $V_{IN} = 1.8\text{V}$	45	—	180	μA
I_{CCADC}	Analog supply current, analog circuits in powered up state	—	—	25	mA
$I_{BATT}^{(3)}$	Battery supply current	—	—	150	nA
$R_{IN_TERM}^{(4)}$	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_40) for commercial (C), and industrial (I), and extended (E) temperature devices	28	40	55	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_50) for commercial (C), and industrial (I), and extended (E) temperature devices	35	50	65	Ω
	Thevenin equivalent resistance of programmable input termination to $V_{CCO}/2$ (UNTUNED_SPLIT_60) for commercial (C), and industrial (I), and extended (E) temperature devices	44	60	83	Ω

Table 3: DC Characteristics Over Recommended Operating Conditions (Cont'd)

Symbol	Description	Min	Typ ⁽¹⁾	Max	Units
n	Temperature diode ideality factor	—	1.010	—	—
r	Temperature diode series resistance	—	2	—	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. This measurement represents the die capacitance at the pad, not including the package.
3. Maximum value specified for worst case process at 25°C.
4. Termination resistance to a V_{CCO}/2 level.

Table 4: V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for 3.3V HR I/O Banks⁽¹⁾

AC Voltage Overshoot	% of UI @-40°C to 100°C	AC Voltage Undershoot	% of UI @-40°C to 100°C
V _{CCO} + 0.40	100	-0.40	100
V _{CCO} + 0.45	100	-0.45	61.7
V _{CCO} + 0.50	100	-0.50	25.8
V _{CCO} + 0.55	100	-0.55	11.0
V _{CCO} + 0.60	46.6	-0.60	4.77
V _{CCO} + 0.65	21.2	-0.65	2.10
V _{CCO} + 0.70	9.75	-0.70	0.94
V _{CCO} + 0.75	4.55	-0.75	0.43
V _{CCO} + 0.80	2.15	-0.80	0.20
V _{CCO} + 0.85	1.02	-0.85	0.09
V _{CCO} + 0.90	0.49	-0.90	0.04
V _{CCO} + 0.95	0.24	-0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.

Table 5: Typical Quiescent Supply Current

Symbol	Description	Device	Speed Grade				Units	
			1.0V		0.9V			
			-3	-2/-2L	-1	-2L		
I _{CCINTQ}	Quiescent V _{CCINT} supply current	XC7A100T	155	155	155	108	mA	
		XC7A200T	328	328	328	232	mA	
I _{CCOQ}	Quiescent V _{CCO} supply current	XC7A100T	4	4	4	4	mA	
		XC7A200T	5	5	5	5	mA	
I _{CCAUXQ}	Quiescent V _{CCAUX} supply current	XC7A100T	36	36	36	36	mA	
		XC7A200T	73	73	73	73	mA	
I _{CCBRAMQ}	Quiescent V _{CCBRAM} supply current	XC7A100T	4	4	4	4	mA	
		XC7A200T	11	11	11	11	mA	

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT} , V_{CCBRAM} , V_{CCAUX} , and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers is V_{CCINT} , $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT} , $V_{MGTAVTT}$. There is no recommended sequencing for $V_{MGTAVCAUX}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$ V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to $0.3 \times T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$ V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to $0.3 \times T_{VCCINT}$ (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

Table 6 shows the minimum current, in addition to I_{CCQ} , that is required by Artix-7 devices for proper power-on and configuration. If the current minimums shown in **Table 5** and **Table 6** are met, the device powers on after all four supplies have passed through their power-on reset threshold voltages. The FPGA must not be configured until after V_{CCINT} is applied.

Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 6: Power-On Current for Artix-7 Devices⁽¹⁾

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
	Typ ⁽²⁾	Typ ⁽²⁾	Typ ⁽²⁾	Typ ⁽²⁾	
XC7A100T	$I_{CCINTQ} + 170$	$I_{CCAUXQ} + 40$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 60$	mA
XC7A200T	$I_{CCINTQ} + 340$	$I_{CCAUXQ} + 50$	$I_{CCOQ} + 40$ mA per bank	$I_{CCBRAMQ} + 80$	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at <http://www.xilinx.com/power>) to calculate maximum power-on currents.
2. Typical values are specified at nominal voltage, 25°C.

Table 7: Power Supply Ramp Time

Symbol	Description	Conditions	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$	$T_J = 100^{\circ}\text{C}^{(1)}$	—	500	ms
		$T_J = 85^{\circ}\text{C}^{(1)}$	—	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with worst case V_{CCO} of 3.465V.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: SelectIO DC Input and Output Levels⁽¹⁾⁽²⁾

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V , Min	V , Max	V , Min	V , Max	V , Max	V , Min	mA, Max	mA, Min
HSTL_I	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8.00	-8.00
HSTL_I_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	8.00	-8.00
HSTL_II	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16.00	-16.00
HSTL_II_18	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	16.00	-16.00
HSUL_12	-0.300	$V_{REF} - 0.130$	$V_{REF} + 0.130$	$V_{CCO} + 0.300$	20% V_{CCO}	80% V_{CCO}	0.10	-0.10
LVCMOS12	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 3	Note 3
LVCMOS15	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18	-0.300	35% V_{CCO}	65% V_{CCO}	$V_{CCO} + 0.300$	0.450	$V_{CCO} - 0.450$	Note 5	Note 5
LVCMOS25	-0.300	0.7	1.700	$V_{CCO} + 0.300$	0.400	$V_{CCO} - 0.400$	Note 4	Note 4
LVCMOS33	-0.300	0.8	2.000	3.450	0.400	$V_{CCO} - 0.400$	Note 4	Note 4
LVTTL	-0.300	0.8	2.000	3.450	0.400	2.400	Note 5	Note 5
MOBILE_DDR	-0.300	20% V_{CCO}	80% V_{CCO}	$V_{CCO} + 0.300$	10% V_{CCO}	90% V_{CCO}	0.10	-0.10
PCI33_3	-0.500	30% V_{CCO}	50% V_{CCO}	$V_{CCO} + 0.500$	10% V_{CCO}	90% V_{CCO}	1.50	-0.50
SSTL135	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	13.00	-13.00
SSTL135_R	-0.300	$V_{REF} - 0.090$	$V_{REF} + 0.090$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.150$	$V_{CCO}/2 + 0.150$	8.90	-8.90
SSTL15	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	13.00	-13.00
SSTL15_R	-0.300	$V_{REF} - 0.100$	$V_{REF} + 0.100$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.175$	$V_{CCO}/2 + 0.175$	8.90	-8.90
SSTL18_I	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.470$	$V_{CCO}/2 + 0.470$	8.00	-8.00
SSTL18_II	-0.300	$V_{REF} - 0.125$	$V_{REF} + 0.125$	$V_{CCO} + 0.300$	$V_{CCO}/2 - 0.600$	$V_{CCO}/2 + 0.600$	13.40	-13.40

Notes:

- Tested according to relevant specifications.
- 3.3V and 2.5V standards are only supported in 3.3V I/O banks.
- Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
- Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
- Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.
- For detailed interface specific DC voltage levels, see [UG471: 7 Series FPGAs SelectIO Resources User Guide](#).

Table 9: Differential SelectIO DC Input and Output Levels

I/O Standard	V _{ICM} ⁽¹⁾			V _{ID} ⁽²⁾			V _{OCM} ⁽³⁾			V _{OD} ⁽⁴⁾		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	—	—	—	1.250	—	Note 5		
MINI_LVDS_25	0.300	1.200	V _{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V _{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V _{CCO} –0.405	V _{CCO} –0.300	V _{CCO} –0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – \bar{Q}).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q – \bar{Q}).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.

Table 10: Complementary Differential SelectIO DC Input and Output Levels

I/O Standard	V _{ICM} ⁽¹⁾			V _{ID} ⁽²⁾		V _{OL} ⁽³⁾		V _{OH} ⁽⁴⁾		I _{OL}	I _{OH}
	V, Min	V, Typ	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min		
DIFF_HSTL_I	0.300	0.750	1.125	0.100	—	0.400	V _{CCO} –0.400	8.00	–8.00		
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	—	0.400	V _{CCO} –0.400	8.00	–8.00		
DIFF_HSTL_II	0.300	0.750	1.125	0.100	—	0.400	V _{CCO} –0.400	16.00	–16.00		
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	—	0.400	V _{CCO} –0.400	16.00	–16.00		
DIFF_HSUL_12	0.300	0.600	0.850	0.100	—	20% V _{CCO}	80% V _{CCO}	0.100	–0.100		
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	—	10% V _{CCO}	90% V _{CCO}	0.100	–0.100		
DIFF_SSTL135	0.300	0.675	1.000	0.100	—	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	13.0	–13.0		
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	—	(V _{CCO} /2) – 0.150	(V _{CCO} /2) + 0.150	8.9	–8.9		
DIFF_SSTL15	0.300	0.750	1.125	0.100	—	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	13.0	–13.0		
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	—	(V _{CCO} /2) – 0.175	(V _{CCO} /2) + 0.175	8.9	–8.9		
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	—	(V _{CCO} /2) – 0.470	(V _{CCO} /2) + 0.470	8.00	–8.00		
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	—	(V _{CCO} /2) – 0.600	(V _{CCO} /2) + 0.600	13.4	–13.4		

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q – \bar{Q}).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

See [UG471: 7 Series FPGAs SelectIO Resources User Guide](#) for more information on the LVDS_25 standard in the HR I/O banks.

Table 11: LVDS_25 DC Specifications

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.375	2.500	2.625	V
V_{OH}	Output High Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and \bar{Q}	$R_T = 100 \Omega$ across Q and \bar{Q} signals	0.700	–	–	V
V_{ODIFF}	Differential Output Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High	$R_T = 100 \Omega$ across Q and \bar{Q} signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage	$R_T = 100 \Omega$ across Q and \bar{Q} signals	1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage ($Q - \bar{Q}$), Q = High ($\bar{Q} - Q$), \bar{Q} = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.300	1.200	1.425	V

AC Switching Characteristics

All values represented in this data sheet are based on the speed specifications in v1.07 from the 14.4/2012.4 device pack for ISE® Design Suite14.4 and Vivado® Design Suite 2012.4 for the -3, -2, -2L (1.0V), and -1 speed grades and v1.05 from the 14.4/2012.4 device pack for the -2L (0.9V) speed grade.

Switching characteristics are specified on a per-speed-grade basis and can be designated as Advance, Preliminary, or Production. Each designation is defined as follows:

Advance Product Specification

These specifications are based on simulations only and are typically available soon after device design specifications are frozen. Although speed grades with this designation are considered relatively stable and conservative, some under-reporting might still occur.

Preliminary Product Specification

These specifications are based on complete ES (engineering sample) silicon characterization. Devices and speed grades with this designation are intended to give a better indication of the expected performance of production silicon. The probability of under-reporting delays is greatly reduced as compared to Advance data.

Production Product Specification

These specifications are released once enough production silicon of a particular device family member has been characterized to provide full correlation between specifications and devices over numerous production lots. There is no under-reporting of delays, and customers receive formal notification of any subsequent changes. Typically, the slowest speed grades transition to Production before faster speed grades.

Testing of AC Switching Characteristics

Internal timing parameters are derived from measuring internal test patterns. All AC switching characteristics are representative of worst-case supply voltage and junction temperature conditions.

For more specific, more precise, and worst-case guaranteed data, use the values reported by the static timing analyzer and back-annotate to the simulation net list. Unless otherwise noted, values apply to all Artix-7 FPGAs.

Speed Grade Designations

Since individual family members are produced at different times, the migration from one category to another depends completely on the status of the fabrication process for each device. [Table 12](#) correlates the current status of each Artix-7 device on a per speed grade basis.

[Table 12: Artix-7 Device Speed Grade Designations](#)

Device	Speed Grade Designations		
	Advance	Preliminary	Production
XC7A100T	-2L (0.9V)		-3, -2, -2L (1.0V), -1
XC7A200T	-2L (0.9V)		-3, -2, -2L (1.0V), -1

Production Silicon and ISE Software Status

In some cases, a particular family member (and speed grade) is released to production before a speed specification is released with the correct label (Advance, Preliminary, Production). Any labeling discrepancies are corrected in subsequent speed specification releases.

[Table 13](#) lists the production released Artix-7 device, speed grade, and the minimum corresponding supported speed specification version and ISE software revisions. The ISE software and speed specifications listed are the minimum releases required for production. All subsequent releases of software and speed specifications are valid.

[Table 13: Artix-7 Device Production Software and Speed Specification Release](#)

Device	Speed Grade			
	1.0V			0.9V
	-3	-2/-2L	-1	-2L
XC7A100T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07			
XC7A200T	ISE 14.4 and Vivado 2012.4 with the 14.4/2012.4 device pack v1.07			

Notes:

- Blank entries indicate a device and/or speed grade in advance or preliminary status.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Artix-7 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the [AC Switching Characteristics, page 9](#).

Table 14: Networking Applications Interface Performances

Description	Speed Grade				Units	
	1.0V		0.9V			
	-3	-2/-2L	-1	-2L		
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	680	680	600	600	Mb/s	
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 14)	1250	1250	950	950	Mb/s	
SDR LVDS receiver (SFI-4.1) ⁽¹⁾	680	680	600	600	Mb/s	
DDR LVDS receiver (SPI-4.2) ⁽¹⁾	1250	1250	950	950	Mb/s	

Notes:

- LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 15: Maximum Physical Interface (PHY) Rate for Memory Interfaces⁽¹⁾⁽²⁾

Memory Standard	Speed Grade				Units	
	1.0V		0.9V			
	-3	-2/-2L	-1	-2L		
4:1 Memory Controllers						
DDR3	1066	800	800	800	Mb/s	
DDR3L	800	800	667	667	Mb/s	
DDR2	800	800	667	667	Mb/s	
LPDDR2	667	667	533	533	Mb/s	
2:1 Memory Controllers						
DDR3	800	700	620	620	Mb/s	
DDR3L	800	700	620	620	Mb/s	
DDR2	800	700	620	620	Mb/s	

Notes:

- V_{REF} tracking is required. For more information, see [UG586, 7 Series FPGAs Memory Interface Solutions User Guide](#).
- When using the internal V_{REF} the maximum data rate is 800 Mb/s (400 MHz).

IOB Pad Input/Output/3-State

Table 16 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOP} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 16: 3.3V IOB High Range (HR) Switching Characteristics

I/O Standard	T_{IOP}				T_{IOOP}				T_{IOTP}				Units	
	Speed Grade				Speed Grade				Speed Grade					
	1.0V		0.9V		1.0V		0.9V		1.0V		0.9V			
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L		
LVTTL_S4	1.26	1.34	1.41	1.58	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns	
LVTTL_S8	1.26	1.34	1.41	1.58	3.54	3.66	3.92	4.15	4.11	4.32	4.75	4.80	ns	
LVTTL_S12	1.26	1.34	1.41	1.58	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns	
LVTTL_S16	1.26	1.34	1.41	1.58	3.07	3.19	3.45	3.68	3.64	3.85	4.28	4.33	ns	
LVTTL_S24	1.26	1.34	1.41	1.58	3.29	3.41	3.67	3.90	3.86	4.07	4.50	4.55	ns	
LVTTL_F4	1.26	1.34	1.41	1.58	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns	
LVTTL_F8	1.26	1.34	1.41	1.58	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns	
LVTTL_F12	1.26	1.34	1.41	1.58	2.73	2.85	3.10	3.33	3.29	3.51	3.93	3.98	ns	
LVTTL_F16	1.26	1.34	1.41	1.58	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns	
LVTTL_F24	1.26	1.34	1.41	1.58	2.52	2.65	2.90	3.22	3.09	3.31	3.73	3.87	ns	
LVDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns	
MINI_LVDS_25	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns	
BLVDS_25	0.73	0.81	0.88	0.90	1.84	1.96	2.21	2.44	2.40	2.62	3.04	3.09	ns	
RSDS_25 (point to point)	0.73	0.81	0.88	0.90	1.27	1.40	1.65	1.88	1.84	2.06	2.48	2.53	ns	
PPDS_25	0.73	0.81	0.88	0.90	1.29	1.41	1.67	1.88	1.86	2.07	2.49	2.53	ns	
TMDS_33	0.73	0.81	0.88	0.90	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns	
PCI33_3	1.24	1.32	1.39	1.57	3.10	3.22	3.48	3.71	3.67	3.88	4.31	4.36	ns	
HSUL_12	0.67	0.75	0.82	0.87	1.80	1.93	2.18	2.41	2.37	2.59	3.01	3.06	ns	
DIFF_HSUL_12	0.68	0.76	0.83	0.88	1.80	1.93	2.18	2.21	2.37	2.59	3.01	2.86	ns	
HSTL_I_S	0.67	0.75	0.82	0.87	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns	
HSTL_II_S	0.65	0.73	0.80	0.85	1.41	1.54	1.79	1.99	1.98	2.20	2.62	2.64	ns	
HSTL_I_18_S	0.67	0.75	0.82	0.87	1.29	1.41	1.67	1.86	1.86	2.07	2.49	2.51	ns	
HSTL_II_18_S	0.66	0.75	0.81	0.87	1.41	1.54	1.79	1.97	1.98	2.20	2.62	2.62	ns	
DIFF_HSTL_I_S	0.68	0.76	0.83	0.85	1.59	1.71	1.96	2.13	2.15	2.37	2.79	2.78	ns	
DIFF_HSTL_II_S	0.68	0.76	0.83	0.85	1.51	1.63	1.88	2.07	2.08	2.29	2.71	2.72	ns	
DIFF_HSTL_I_18_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.96	1.95	2.17	2.59	2.61	ns	
DIFF_HSTL_II_18_S	0.70	0.78	0.85	0.87	1.46	1.58	1.84	2.00	2.03	2.24	2.67	2.65	ns	
HSTL_I_F	0.67	0.75	0.82	0.87	1.10	1.22	1.48	1.69	1.67	1.88	2.31	2.34	ns	

Table 16: 3.3V IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T _{IOP1}				T _{IOOP}				T _{IOTP}				Units	
	Speed Grade				Speed Grade				Speed Grade					
	1.0V		0.9V		1.0V		0.9V		1.0V		0.9V			
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L		
HSTL_II_F	0.65	0.73	0.80	0.85	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns	
HSTL_I_18_F	0.67	0.75	0.82	0.87	1.13	1.26	1.51	1.72	1.70	1.92	2.34	2.37	ns	
HSTL_II_18_F	0.66	0.75	0.81	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns	
DIFF_HSTL_I_F	0.68	0.76	0.83	0.85	1.18	1.30	1.56	1.77	1.75	1.96	2.39	2.42	ns	
DIFF_HSTL_II_F	0.68	0.76	0.83	0.85	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns	
DIFF_HSTL_I_18_F	0.71	0.79	0.86	0.87	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns	
DIFF_HSTL_II_18_F	0.70	0.78	0.85	0.87	1.21	1.33	1.59	1.77	1.78	1.99	2.42	2.42	ns	
LVCMOS33_S4	1.26	1.34	1.41	1.62	3.80	3.93	4.18	4.41	4.37	4.59	5.01	5.06	ns	
LVCMOS33_S8	1.26	1.34	1.41	1.62	3.52	3.65	3.90	4.13	4.09	4.31	4.73	4.78	ns	
LVCMOS33_S12	1.26	1.34	1.41	1.62	3.09	3.21	3.46	3.69	3.65	3.87	4.29	4.34	ns	
LVCMOS33_S16	1.26	1.34	1.41	1.62	3.40	3.52	3.77	4.00	3.97	4.18	4.60	4.65	ns	
LVCMOS33_F4	1.26	1.34	1.41	1.62	3.26	3.38	3.64	3.86	3.83	4.04	4.46	4.51	ns	
LVCMOS33_F8	1.26	1.34	1.41	1.62	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns	
LVCMOS33_F12	1.26	1.34	1.41	1.62	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns	
LVCMOS33_F16	1.26	1.34	1.41	1.62	2.55	2.68	2.93	3.16	3.12	3.34	3.76	3.81	ns	
LVCMOS25_S4	1.12	1.20	1.27	1.43	3.13	3.26	3.51	3.72	3.70	3.91	4.34	4.37	ns	
LVCMOS25_S8	1.12	1.20	1.27	1.43	2.88	3.01	3.26	3.49	3.45	3.67	4.09	4.14	ns	
LVCMOS25_S12	1.12	1.20	1.27	1.43	2.48	2.60	2.85	3.08	3.05	3.26	3.68	3.73	ns	
LVCMOS25_S16	1.12	1.20	1.27	1.43	2.82	2.94	3.20	3.43	3.39	3.60	4.03	4.08	ns	
LVCMOS25_F4	1.12	1.20	1.27	1.43	2.74	2.87	3.12	3.35	3.31	3.52	3.95	4.00	ns	
LVCMOS25_F8	1.12	1.20	1.27	1.43	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns	
LVCMOS25_F12	1.12	1.20	1.27	1.43	2.16	2.29	2.54	2.77	2.73	2.95	3.37	3.42	ns	
LVCMOS25_F16	1.12	1.20	1.27	1.43	2.01	2.13	2.39	2.61	2.58	2.79	3.21	3.26	ns	
LVCMOS18_S4	0.74	0.83	0.89	0.94	1.62	1.74	1.99	2.19	2.19	2.40	2.82	2.84	ns	
LVCMOS18_S8	0.74	0.83	0.89	0.94	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns	
LVCMOS18_S12	0.74	0.83	0.89	0.94	2.18	2.30	2.56	2.79	2.75	2.96	3.39	3.44	ns	
LVCMOS18_S16	0.74	0.83	0.89	0.94	1.52	1.65	1.90	2.13	2.09	2.31	2.73	2.78	ns	
LVCMOS18_S24	0.74	0.83	0.89	0.94	1.60	1.72	1.98	2.21	2.17	2.38	2.81	2.86	ns	
LVCMOS18_F4	0.74	0.83	0.89	0.94	1.45	1.57	1.82	2.05	2.01	2.23	2.65	2.70	ns	
LVCMOS18_F8	0.74	0.83	0.89	0.94	1.68	1.80	2.06	2.29	2.25	2.46	2.89	2.94	ns	
LVCMOS18_F12	0.74	0.83	0.89	0.94	1.68	1.80	2.06	2.29	2.25	2.46	2.89	2.94	ns	
LVCMOS18_F16	0.74	0.83	0.89	0.94	1.40	1.52	1.77	2.00	1.97	2.18	2.60	2.65	ns	
LVCMOS18_F24	0.74	0.83	0.89	0.94	1.34	1.46	1.71	1.94	1.90	2.12	2.54	2.59	ns	
LVCMOS15_S4	0.77	0.86	0.93	0.98	2.05	2.18	2.43	2.50	2.62	2.84	3.26	3.15	ns	
LVCMOS15_S8	0.77	0.86	0.93	0.98	2.09	2.21	2.46	2.69	2.65	2.87	3.29	3.34	ns	
LVCMOS15_S12	0.77	0.86	0.93	0.98	1.59	1.71	1.96	2.19	2.15	2.37	2.79	2.84	ns	
LVCMOS15_S16	0.77	0.86	0.93	0.98	1.59	1.71	1.96	2.19	2.15	2.37	2.79	2.84	ns	

Table 16: 3.3V IOB High Range (HR) Switching Characteristics (Cont'd)

I/O Standard	T _{IOPI}				T _{IOOP}				T _{IOTP}				Units	
	Speed Grade				Speed Grade				Speed Grade					
	1.0V		0.9V		1.0V		0.9V		1.0V		0.9V			
	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L	-3	-2/-2L	-1	-2L		
LVCMOS15_F4	0.77	0.86	0.93	0.98	1.85	1.97	2.23	2.27	2.42	2.63	3.06	2.92	ns	
LVCMOS15_F8	0.77	0.86	0.93	0.98	1.60	1.72	1.98	2.21	2.17	2.38	2.81	2.86	ns	
LVCMOS15_F12	0.77	0.86	0.93	0.98	1.35	1.47	1.73	1.96	1.92	2.13	2.56	2.61	ns	
LVCMOS15_F16	0.77	0.86	0.93	0.98	1.34	1.46	1.71	1.94	1.90	2.12	2.54	2.59	ns	
LVCMOS12_S4	0.87	0.95	1.02	1.08	2.57	2.69	2.95	3.18	3.14	3.35	3.78	3.83	ns	
LVCMOS12_S8	0.87	0.95	1.02	1.08	2.09	2.21	2.46	2.69	2.65	2.87	3.29	3.34	ns	
LVCMOS12_S12	0.87	0.95	1.02	1.08	1.79	1.91	2.17	2.40	2.36	2.57	2.99	3.05	ns	
LVCMOS12_F4	0.87	0.95	1.02	1.08	1.98	2.10	2.35	2.58	2.54	2.76	3.18	3.23	ns	
LVCMOS12_F8	0.87	0.95	1.02	1.08	1.54	1.66	1.92	2.15	2.11	2.32	2.75	2.80	ns	
LVCMOS12_F12	0.87	0.95	1.02	1.08	1.38	1.51	1.76	1.97	1.95	2.16	2.59	2.62	ns	
SSTL135_S	0.67	0.75	0.82	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns	
SSTL15_S	0.60	0.68	0.75	0.80	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns	
SSTL18_I_S	0.67	0.75	0.82	0.87	1.67	1.79	2.04	2.24	2.23	2.45	2.87	2.89	ns	
SSTL18_II_S	0.67	0.75	0.82	0.87	1.31	1.43	1.68	1.91	1.87	2.09	2.51	2.56	ns	
DIFF_SSTL135_S	0.68	0.76	0.83	0.87	1.35	1.47	1.73	1.93	1.92	2.13	2.56	2.58	ns	
DIFF_SSTL15_S	0.68	0.76	0.83	0.87	1.30	1.43	1.68	1.88	1.87	2.09	2.51	2.53	ns	
DIFF_SSTL18_I_S	0.71	0.79	0.86	0.87	1.68	1.80	2.06	2.24	2.25	2.46	2.89	2.89	ns	
DIFF_SSTL18_II_S	0.71	0.79	0.86	0.87	1.38	1.51	1.76	1.94	1.95	2.17	2.59	2.59	ns	
SSTL135_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns	
SSTL15_F	0.60	0.68	0.75	0.80	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns	
SSTL18_I_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.72	1.69	1.90	2.32	2.37	ns	
SSTL18_II_F	0.67	0.75	0.82	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns	
DIFF_SSTL135_F	0.68	0.76	0.83	0.87	1.12	1.24	1.49	1.71	1.69	1.90	2.32	2.36	ns	
DIFF_SSTL15_F	0.68	0.76	0.83	0.87	1.07	1.19	1.45	1.68	1.64	1.85	2.28	2.33	ns	
DIFF_SSTL18_I_F	0.71	0.79	0.86	0.87	1.23	1.35	1.60	1.80	1.79	2.01	2.43	2.45	ns	
DIFF_SSTL18_II_F	0.71	0.79	0.86	0.87	1.21	1.33	1.59	1.79	1.78	1.99	2.42	2.44	ns	

Table 17 specifies the values of T_{IOTPHZ} and T_{IOIBUFDISABLE}. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). T_{IOIBUFDISABLE} is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 17: IOB 3-state Output Switching Characteristics

Symbol	Description	Speed Grade				Units	
		1.0V		0.9V			
		-3	-2/-2L	-1	-2L		
T _{IOTPHZ}	T input to pad high-impedance	2.06	2.19	2.37	2.19	ns	
T _{IOIBUFDISABLE}	IBUF turn-on time from IBUFDISABLE to O output	2.11	2.30	2.60	2.30	ns	

Input/Output Logic Switching Characteristics

Table 18: ILOGIC Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T _{ICE1CK} /T _{ICKCE1}	CE1 pin setup/hold with respect to CLK	0.48/0.02	0.54/0.02	0.76/0.02	0.40/-0.07	ns
T _{ISRCK} /T _{ICKSR}	SR pin setup/hold with respect to CLK	0.60/0.01	0.70/0.01	1.13/0.01	0.88/-0.35	ns
T _{IDOCK} /T _{IOCKD}	D pin setup/hold with respect to CLK without Delay	0.01/0.27	0.01/0.29	0.01/0.33	0.01/0.33	ns
T _{IDOCKD} /T _{IOCKDD}	DDLY pin setup/hold with respect to CLK (using IDELAY)	0.02/0.27	0.02/0.29	0.02/0.33	0.01/0.33	ns
Combinatorial						
T _{IDI}	D pin to O pin propagation delay, no Delay	0.11	0.11	0.13	0.14	ns
T _{IDID}	DDLY pin to O pin propagation delay (using IDELAY)	0.11	0.12	0.14	0.15	ns
Sequential Delays						
T _{IDLO}	D pin to Q1 pin using flip-flop as a latch without Delay	0.41	0.44	0.51	0.54	ns
T _{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY)	0.41	0.44	0.51	0.55	ns
T _{ICKQ}	CLK to Q outputs	0.53	0.57	0.66	0.71	ns
T _{RQ_ILOGIC}	SR pin to OQ/TQ out	0.96	1.08	1.32	1.32	ns
T _{GSRQ_ILOGIC}	Global set/reset to Q outputs	7.60	7.60	10.51	11.39	ns
Set/Reset						
T _{RPW_ILOGIC}	Minimum pulse width, SR inputs	0.61	0.72	0.72	0.68	ns, Min

Table 19: OLOGIC Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T _{ODCK} /T _{OCKD}	D1/D2 pins setup/hold with respect to CLK	0.67/-0.11	0.71/-0.11	0.84/-0.11	0.60/-0.18	ns
T _{OOCCK} /T _{OCKOCE}	OCE pin setup/hold with respect to CLK	0.32/0.58	0.34/0.58	0.51/0.58	0.21/-0.10	ns
T _{OSRCK} /T _{OCKSR}	SR pin setup/hold with respect to CLK	0.37/0.21	0.44/0.21	0.80/0.21	0.62/-0.25	ns
T _{OTCK} /T _{OCKT}	T1/T2 pins setup/hold with respect to CLK	0.69/-0.14	0.73/-0.14	0.89/-0.14	0.60/-0.18	ns
T _{TCECK} /T _{OCKTCE}	TCE pin setup/hold with respect to CLK	0.32/0.01	0.34/0.01	0.51/0.01	0.22/-0.10	ns
Combinatorial						
T _{ODQ}	D1 to OQ out or T1 to TQ out	0.83	0.96	1.16	1.36	ns
Sequential Delays						
T _{OCKQ}	CLK to OQ/TQ out	0.47	0.49	0.56	0.63	ns
T _{RQ_OLOGIC}	SR pin to OQ/TQ out	0.72	0.80	0.95	1.12	ns
T _{GSRQ_OLOGIC}	Global set/reset to Q outputs	7.60	7.60	10.51	11.39	ns
Set/Reset						
T _{RPW_OLOGIC}	Minimum pulse width, SR inputs	0.64	0.74	0.74	0.68	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 20: ISERDES Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup/Hold for Control Lines						
T _{ISCCCK_BITSILIP} /T _{ISCKC_BITSILIP}	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.14	0.02/0.15	0.02/0.17	0.02/0.21	ns
T _{ISCCCK_CE} / T _{ISCKC_CE} ⁽²⁾	CE pin setup/hold with respect to CLK (for CE1)	0.45/-0.01	0.50/-0.01	0.72/-0.01	0.35/-0.11	ns
T _{ISCCCK_CE2} / T _{ISCKC_CE2} ⁽²⁾	CE pin setup/hold with respect to CLKDIV (for CE2)	-0.10/0.33	-0.10/0.36	-0.10/0.40	-0.17/0.40	ns
Setup/Hold for Data Lines						
T _{ISDCK_D} /T _{ISCKD_D}	D pin setup/hold with respect to CLK	-0.02/0.12	-0.02/0.14	-0.02/0.17	-0.04/0.19	ns
T _{ISDCK_DDLY} /T _{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY) ⁽¹⁾	-0.02/0.12	-0.02/0.14	-0.02/0.17	-0.03/0.19	ns
T _{ISDCK_D_DDR} /T _{ISCKD_D_DDR}	D pin setup/hold with respect to CLK at DDR mode	-0.02/0.12	-0.02/0.14	-0.02/0.17	-0.04/0.19	ns
T _{ISDCK_DDLY_DDR} /T _{ISCKD_DDLY_DDR}	D pin setup/hold with respect to CLK at DDR mode (using IDELAY) ⁽¹⁾	0.12/0.12	0.14/0.14	0.17/0.17	0.19/0.19	ns
Sequential Delays						
T _{ISCKO_Q}	CLKDIV to out at Q pin	0.53	0.54	0.66	0.67	ns
Propagation Delays						
T _{ISDO_DO}	D input to DO output pin	0.11	0.11	0.13	0.14	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCCK_CE}/T_{ISCKC_CE} in TRACE report.

Output Serializer/Deserializer Switching Characteristics

Table 21: OSERDES Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup/Hold						
T _{OSDCK_D} /T _{OSCKD_D}	D input setup/hold with respect to CLKDIV	0.42/0.03	0.45/0.03	0.63/0.03	0.44/-0.25	ns
T _{OSDCK_T} /T _{OSCKD_T} ⁽¹⁾	T input setup/hold with respect to CLK	0.69/-0.13	0.73/-0.13	0.88/-0.13	0.60/-0.25	ns
T _{OSDCK_T2} /T _{OSCKD_T2} ⁽¹⁾	T input setup/hold with respect to CLKDIV	0.31/-0.13	0.34/-0.13	0.39/-0.13	0.46/-0.25	ns
T _{oscck_oce} /T _{osckc_oce}	OCE input setup/hold with respect to CLK	0.32/0.58	0.34/0.58	0.51/0.58	0.21/-0.15	ns
T _{oscck_s}	SR (reset) input setup with respect to CLKDIV	0.47	0.52	0.85	0.70	ns
T _{oscck_tce} /T _{osckc_tce}	TCE input setup/hold with respect to CLK	0.32/0.01	0.34/0.01	0.51/0.01	0.22/-0.15	ns
Sequential Delays						
T _{osccko_oq}	Clock to out from CLK to OQ	0.40	0.42	0.48	0.54	ns
T _{osccko_tq}	Clock to out from CLK to TQ	0.47	0.49	0.56	0.63	ns
Combinatorial						
T _{osdo_ttq}	T input to TQ Out	0.83	0.92	1.11	1.18	ns

Notes:

- T_{OSDCK_T2} and T_{OSCKD_T2} are reported as T_{OSDCK_T}/T_{OSCKD_T} in TRACE report.

Input/Output Delay Switching Characteristics

Table 22: Input/Output Delay Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
IDELAYCTRL						
T_DLYCCO_RDY	Reset to ready for IDELAYCTRL	3.67	3.67	3.67	3.22	μs
F_IDELAYCTRL_REF	Attribute REFCLK frequency = 200.00 ⁽¹⁾	200.00	200.00	200.00	200.00	MHz
	Attribute REFCLK frequency = 300.00 ⁽¹⁾	300.00	300.00	N/A	N/A	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
T_IDELAYCTRL_RPW	Minimum Reset pulse width	59.28	59.28	59.28	52.00	ns
IDELAY						
T_IDELAYRESOLUTION	IDELAY chain delay resolution	1/(32 x 2 x F _{REF})				ps
T_IDELAYPAT_JIT	Pattern dependent period jitter in delay chain for clock pattern. ⁽²⁾	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽³⁾	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23) ⁽⁴⁾	±9	±9	±9	±9	ps per tap
T_IDELAY_CLK_MAX	Maximum frequency of CLK input to IDELAY	680.00	680.00	600.00	520.00	MHz
T_IDCCK_CE / T_IDCKC_CE	CE pin setup/hold with respect to C for IDELAY	0.12/0.11	0.16/0.13	0.21/0.16	0.14/0.16	ns
T_IDCCK_INC / T_IDCKC_INC	INC pin setup/hold with respect to C for IDELAY	0.12/0.16	0.14/0.18	0.16/0.22	0.10/0.23	ns
T_IDCCK_RST / T_IDCKC_RST	RST pin setup/hold with respect to C for IDELAY	0.15/0.09	0.16/0.11	0.18/0.14	0.22/0.19	ns
T_IDDO_IDATAIN	Propagation delay through IDELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE.
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IDELAY tap setting. See TRACE report for actual values.

Table 23: IO_FIFO Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
IO_FIFO Clock to Out Delays						
T _{OFFCKO_DO}	RDCLK to Q outputs	0.55	0.60	0.68	0.81	ns
T _{CKO_FLAGS}	Clock to IO_FIFO flags	0.55	0.61	0.77	0.55	ns
Setup/Hold						
T _{CCK_D/T_{CKC_D}}	D inputs to WRCLK	0.47/0.02	0.51/0.02	0.58/0.02	0.76/-0.05	ns
T _{IFFCCK_WREN/T_{IFFCKC_WREN}}	WREN to WRCLK	0.42/-0.01	0.47/-0.01	0.53/-0.01	0.70/-0.05	ns
T _{OFFCCK_RDEN/T_{OFFCKC_RDEN}}	RDEN to RDCLK	0.53/0.02	0.58/0.02	0.66/0.02	0.79/-0.02	ns
Minimum Pulse Width						
T _{PWH_IO_FIFO}	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
T _{PWL_IO_FIFO}	RESET, RDCLK, WRCLK	1.62	2.15	2.15	2.15	ns
Maximum Frequency						
F _{MAX}	RDCLK and WRCLK	266.67	200.00	200.00	200.00	MHz

CLB Switching Characteristics

Table 24: CLB Switching Characteristics

Symbol	Description	Speed Grade				Units	
		1.0V		0.9V			
		-3	-2/-2L	-1	-2L		
Combinatorial Delays							
T _{ILO}	An – Dn LUT address to A	0.10	0.11	0.13	0.15	ns, Max	
T _{ILO_2}	An – Dn LUT address to AMUX/CMUX	0.27	0.30	0.36	0.41	ns, Max	
T _{ILO_3}	An – Dn LUT address to BMUX_A	0.42	0.46	0.55	0.65	ns, Max	
T _{I TO}	An – Dn inputs to A – D Q outputs	0.94	1.05	1.27	1.51	ns, Max	
T _{AXA}	AX inputs to AMUX output	0.62	0.69	0.84	1.01	ns, Max	
T _{AXB}	AX inputs to BMUX output	0.58	0.66	0.83	0.98	ns, Max	
T _{AXC}	AX inputs to CMUX output	0.60	0.68	0.82	0.98	ns, Max	
T _{AXD}	AX inputs to DMUX output	0.68	0.75	0.90	1.08	ns, Max	
T _{BXB}	BX inputs to BMUX output	0.51	0.57	0.69	0.82	ns, Max	
T _{BXD}	BX inputs to DMUX output	0.62	0.69	0.82	0.99	ns, Max	
T _{CXC}	CX inputs to CMUX output	0.42	0.48	0.58	0.69	ns, Max	
T _{CXD}	CX inputs to DMUX output	0.53	0.59	0.71	0.86	ns, Max	
T _{DXD}	DX inputs to DMUX output	0.52	0.58	0.70	0.84	ns, Max	
Sequential Delays							
T _{CKO}	Clock to AQ – DQ outputs	0.40	0.44	0.53	0.62	ns, Max	
T _{SHCKO}	Clock to AMUX – DMUX outputs	0.47	0.53	0.66	0.73	ns, Max	
Setup and Hold Times of CLB Flip-Flops Before/After Clock CLK							
T _{AS/T_{AH}}	A _N – D _N input to CLK on A – D flip-flops	0.07/0.12	0.09/0.14	0.11/0.18	0.11/0.20	ns, Min	
T _{DICK/T_{CKDI}}	A _X – D _X input to CLK on A – D flip-flops	0.06/0.19	0.07/0.21	0.09/0.26	0.09/0.31	ns, Min	
	A _X – D _X input through MUXs and/or carry logic to CLK on A – D flip-flops	0.59/0.08	0.66/0.09	0.81/0.11	0.97/0.12	ns, Min	
T _{CECK_CLB/} T _{CKCE_CLB}	CE input to CLK on A – D flip-flops	0.15/0.00	0.17/0.00	0.21/0.01	0.34/–0.01	ns, Min	
T _{SRCK/T_{CKSR}}	SR input to CLK on A – D flip-flops	0.38/0.03	0.43/0.04	0.53/0.05	0.62/0.05	ns, Min	
Set/Reset							
T _{SRMIN}	SR input minimum pulse width	0.52	0.78	1.04	0.95	ns, Min	
T _{RQ}	Delay from SR input to AQ – DQ flip-flops	0.53	0.59	0.71	0.83	ns, Max	
T _{CEO}	Delay from CE input to AQ – DQ flip-flops	0.52	0.58	0.70	0.83	ns, Max	
F _{TOG}	Toggle frequency (for export control)	1412	1286	1098	1098	MHz	

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 25: CLB Distributed RAM Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T _{SHCKO}	Clock to A – B outputs	0.98	1.09	1.32	1.54	ns, Max
T _{SHCKO_1}	Clock to AMUX – BMUX outputs	1.37	1.53	1.86	2.18	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{DS_LRAM} /T _{DH_LRAM}	A – D inputs to CLK	0.54/0.28	0.60/0.30	0.72/0.35	0.96/0.40	ns, Min
T _{AS_LRAM} /T _{AH_LRAM}	Address An inputs to clock	0.27/0.55	0.30/0.60	0.37/0.70	0.43/0.71	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.69/0.18	0.77/0.21	0.94/0.26	1.11/0.29	ns, Min
T _{WS_LRAM} /T _{WH_LRAM}	WE input to clock	0.38/0.10	0.43/0.12	0.53/0.17	0.62/0.13	ns, Min
T _{CECK_LRAM} / T _{CKCE_LRAM}	CE input to CLK	0.39/0.10	0.44/0.11	0.53/0.17	0.63/0.12	ns, Min
Clock CLK						
T _{MPW_LRAM}	Minimum pulse width	1.05	1.13	1.25	0.82	ns, Min
T _{MCP}	Minimum clock period	2.10	2.26	2.50	1.64	ns, Min

Notes:

1. A Zero "0" Hold Time listing indicates no hold time or a negative hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 26: CLB Shift Register Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Sequential Delays						
T _{REG}	Clock to A – D outputs	1.19	1.33	1.61	1.89	ns, Max
T _{REG_MUX}	Clock to AMUX – DMUX output	1.58	1.77	2.15	2.53	ns, Max
T _{REG_M31}	Clock to DMUX output via M31 output	1.12	1.23	1.46	1.68	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{WS_SHFREG} / T _{WH_SHFREG}	WE input	0.37/0.10	0.41/0.12	0.51/0.17	0.59/0.13	ns, Min
T _{CECK_SHFREG} / T _{CKCE_SHFREG}	CE input to CLK	0.37/0.10	0.42/0.11	0.52/0.17	0.60/0.12	ns, Min
T _{DS_SHFREG} / T _{DH_SHFREG}	A – D inputs to CLK	0.33/0.34	0.37/0.37	0.44/0.43	0.54/0.47	ns, Min
Clock CLK						
T _{MPW_SHFREG}	Minimum pulse width	0.77	0.86	0.98	1.04	ns, Min

Notes:

1. A Zero "0" Hold Time listing indicates no hold time or a negative hold time.

Block RAM and FIFO Switching Characteristics

Table 27: Block RAM and FIFO Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Block RAM and FIFO Clock-to-Out Delays						
T _{RCKO_DO} and T _{RCKO_DO_REG} ⁽¹⁾	Clock CLK to DOUT output (without output register) ⁽²⁾⁽³⁾	1.85	2.13	2.46	2.87	ns, Max
	Clock CLK to DOUT output (with output register) ⁽⁴⁾⁽⁵⁾	0.64	0.74	0.89	1.02	ns, Max
T _{RCKO_DO_ECC} and T _{RCKO_DO_ECC_REG}	Clock CLK to DOUT output with ECC (without output register) ⁽²⁾⁽³⁾	2.77	3.04	3.84	5.30	ns, Max
	Clock CLK to DOUT output with ECC (with output register) ⁽⁴⁾⁽⁵⁾	0.73	0.81	0.94	1.11	ns, Max
T _{RCKO_DO_CASCOUP} and T _{RCKO_DO_CASCOUP_REG}	Clock CLK to DOUT output with cascade (without output register) ⁽²⁾	2.61	2.88	3.30	3.76	ns, Max
	Clock CLK to DOUT output with cascade (with output register) ⁽⁴⁾	1.16	1.28	1.46	1.56	ns, Max
T _{RCKO_FLAGS}	Clock CLK to FIFO flags outputs ⁽⁶⁾	0.76	0.87	1.05	1.14	ns, Max
T _{RCKO_POINTERS}	Clock CLK to FIFO pointers outputs ⁽⁷⁾	0.94	1.02	1.15	1.30	ns, Max
T _{RCKO_PARITY_ECC}	Clock CLK to ECCPARITY in ECC encode only mode	0.78	0.85	0.94	1.10	ns, Max
T _{RCKO_SDBIT_ECC} and T _{RCKO_SDBIT_ECC_REG}	Clock CLK to BITERR (without output register)	2.56	2.81	3.55	4.90	ns, Max
	Clock CLK to BITERR (with output register)	0.68	0.76	0.89	1.05	ns, Max
T _{RCKO_RDADDR_ECC} and T _{RCKO_RDADDR_ECC_REG}	Clock CLK to RDADDR output with ECC (without output register)	0.75	0.88	1.07	1.15	ns, Max
	Clock CLK to RDADDR output with ECC (with output register)	0.84	0.93	1.08	1.29	ns, Max
Setup and Hold Times Before/After Clock CLK						
T _{RCKC_ADDRA} /T _{RCKC_ADDRA}	ADDR inputs ⁽⁸⁾	0.45/0.31	0.49/0.33	0.57/0.36	0.77/0.45	ns, Min
T _{RDCK_DI_WF_NC} /T _{RCKD_DI_WF_NC}	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode ⁽⁹⁾	0.58/0.60	0.65/0.63	0.74/0.67	0.92/0.76	ns, Min
T _{RDCK_DI_RF} /T _{RCKD_DI_RF}	Data input setup/hold time when block RAM is configured in READ_FIRST mode ⁽⁹⁾	0.20/0.29	0.22/0.34	0.25/0.41	0.29/0.38	ns, Min
T _{RDCK_DI_ECC} /T _{RCKD_DI_ECC}	DIN inputs with block RAM ECC in standard mode ⁽⁹⁾	0.50/0.43	0.55/0.46	0.63/0.50	0.78/0.54	ns, Min
T _{RDCK_DI_ECCW} /T _{RCKD_DI_ECCW}	DIN inputs with block RAM ECC encode only ⁽⁹⁾	0.93/0.43	1.02/0.46	1.17/0.50	1.38/0.48	ns, Min
T _{RDCK_DI_ECC_FIFO} /T _{RCKD_DI_ECC_FIFO}	DIN inputs with FIFO ECC in standard mode ⁽⁹⁾	1.04/0.56	1.15/0.59	1.32/0.64	1.55/0.77	ns, Min
T _{RCKC_INJECTBITERR} /T _{RCKC_INJECTBITERR}	Inject single/double bit error in ECC mode	0.58/0.35	0.64/0.37	0.74/0.40	0.92/0.48	ns, Min
T _{RCKC_EN} /T _{RCKC_EN}	Block RAM enable (EN) input	0.35/0.20	0.39/0.21	0.45/0.23	0.57/0.26	ns, Min
T _{RCKC_REGCE} /T _{RCKC_REGCE}	CE input of output register	0.24/0.15	0.29/0.15	0.36/0.16	0.40/0.19	ns, Min
T _{RCKC_RSTREG} /T _{RCKC_RSTREG}	Synchronous RSTREG input	0.29/0.07	0.32/0.07	0.35/0.07	0.41/0.07	ns, Min

Table 27: Block RAM and FIFO Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
T _{RCKC_RSTRAM} /T _{RCKC_RSTRAM}	Synchronous RSTRAM input	0.32/0.42	0.34/0.43	0.36/0.46	0.40/0.47	ns, Min
T _{RCKC_WEA} /T _{RCKC_WEA}	Write enable (WE) input (block RAM only)	0.44/0.18	0.48/0.19	0.54/0.20	0.64/0.23	ns, Min
T _{RCKC_WREN} /T _{RCKC_WREN}	WREN FIFO inputs	0.46/0.30	0.46/0.35	0.47/0.43	0.77/0.44	ns, Min
T _{RCKC_RDEN} /T _{RCKC_RDEN}	RDEN FIFO inputs	0.42/0.30	0.43/0.35	0.43/0.43	0.71/0.44	ns, Min
Reset Delays						
T _{RCO_FLAGS}	Reset RST to FIFO flags/pointers ⁽¹⁰⁾	0.90	0.98	1.10	1.25	ns, Max
T _{RREC_RST} /T _{RREM_RST}	FIFO reset recovery and removal timing ⁽¹¹⁾	1.87/-0.81	2.07/-0.81	2.37/-0.81	2.44/-0.71	ns, Max
Maximum Frequency						
F _{MAX_BRAM_WF_NC}	Block RAM (write first and no change modes) when not in SDP RF mode	509.68	460.83	388.20	315.66	MHz
F _{MAX_BRAM_RF_PERFORMANCE}	Block RAM (read first, performance mode) when in SDP RF mode but no address overlap between port A and port B	509.68	460.83	388.20	315.66	MHz
F _{MAX_BRAM_RF_DELAYED_WRITE}	Block RAM (read first, delayed write mode) when in SDP RF mode and there is possibility of overlap between port A and port B addresses	447.63	404.53	339.67	268.96	MHz
F _{MAX_CAS_WF_NC}	Block RAM cascade (write first, no change mode) when cascade but not in RF mode	467.07	418.59	345.78	273.30	MHz
F _{MAX_CAS_RF_PERFORMANCE}	Block RAM cascade (read first, performance mode) when in cascade with RF mode and no possibility of address overlap/one port is disabled	467.07	418.59	345.78	273.30	MHz
F _{MAX_CAS_RF_DELAYED_WRITE}	When in cascade RF mode and there is a possibility of address overlap between port A and port B	405.35	362.19	297.35	226.60	MHz
F _{MAX_FIFO}	FIFO in all modes without ECC	509.68	460.83	388.20	315.66	MHz
F _{MAX_ECC}	Block RAM and FIFO in ECC configuration	410.34	365.10	297.53	215.38	MHz

Notes:

1. TRACE will report all of these parameters as T_{RCKO_DO}.
2. T_{RCKO_DOR} includes T_{RCKO_DOW}, T_{RCKO_DOPR}, and T_{RCKO_DOPW} as well as the B port equivalent timing parameters.
3. These parameters also apply to synchronous FIFO with DO_REG = 0.
4. T_{RCKO_DO} includes T_{RCKO_DOP} as well as the B port equivalent timing parameters.
5. These parameters also apply to multirate (asynchronous) and synchronous FIFO with DO_REG = 1.
6. T_{RCKO_FLAGS} includes the following parameters: T_{RCKO_AEMPTY}, T_{RCKO_AFULL}, T_{RCKO_EMPTY}, T_{RCKO_FULL}, T_{RCKO_RDERR}, T_{RCKO_WRERR}.
7. T_{RCKO_POINTERS} includes both T_{RCKO_RDCOUNT} and T_{RCKO_WRCOUNT}.
8. The ADDR setup and hold must be met when EN is asserted (even when WE is deasserted). Otherwise, block RAM data corruption is possible.
9. These parameters include both A and B inputs as well as the parity inputs of A and B.
10. T_{RCO_FLAGS} includes the following flags: AEMPTY, AFULL, EMPTY, FULL, RDERR, WRERR, RDCOUNT, and WRCOUNT.
11. RDEN and WREN must be held Low prior to and during reset. The FIFO reset must be asserted for at least five positive clock edges of the slowest clock (WRCLK or RDCLK).

DSP48E1 Switching Characteristics

Table 28: DSP48E1 Switching Characteristics

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of Data/Control Pins to the Input Register Clock						
T _{DSPDCK_A_AREG} /T _{DSPCKD_A_AREG}	A input to A register CLK	0.26/ 0.12	0.30/ 0.13	0.37/ 0.14	0.45/ 0.14	ns
T _{DSPDCK_B_BREG} /T _{DSPCKD_B_BREG}	B input to B register CLK	0.33/ 0.15	0.38/ 0.16	0.45/ 0.18	0.60/ 0.19	ns
T _{DSPDCK_C_CREG} /T _{DSPCKD_C_CREG}	C input to C register CLK	0.17/ 0.17	0.20/ 0.19	0.24/ 0.21	0.34/ 0.29	ns
T _{DSPDCK_D_DREG} /T _{DSPCKD_D_DREG}	D input to D register CLK	0.25/ 0.25	0.32/ 0.27	0.42/ 0.27	0.54/ 0.23	ns
T _{DSPDCK_ACIN_AREG} /T _{DSPCKD_ACIN_AREG}	ACIN input to A register CLK	0.23/ 0.12	0.27/ 0.13	0.32/ 0.14	0.36/ 0.14	ns
T _{DSPDCK_BCIN_BREG} /T _{DSPCKD_BCIN_BREG}	BCIN input to B register CLK	0.25/ 0.15	0.29/ 0.16	0.36/ 0.18	0.41/ 0.19	ns
Setup and Hold Times of Data Pins to the Pipeline Register Clock						
T _{DSPDCK_{A,B}_MREG_MULT} / T _{DSPCKD_B_MREG_MULT}	{A, B} input to M register CLK using multiplier	2.40/ -0.01	2.76/ -0.01	3.29/ -0.01	4.31/ -0.07	ns
T _{DSPDCK_{A,B}_ADREG} /T _{DSPCKD_D_ADREG}	{A, D} input to AD register CLK	1.29/ -0.02	1.48/ -0.02	1.76/ -0.02	2.29/ -0.27	ns
Setup and Hold Times of Data/Control Pins to the Output Register Clock						
T _{DSPDCK_{A,B}_PREG_MULT} / T _{DSPCKD_{A,B}_PREG_MULT}	{A, B} input to P register CLK using multiplier	4.02/ -0.28	4.60/ -0.28	5.48/ -0.28	6.95/ -0.48	ns
T _{DSPDCK_D_PREG_MULT} / T _{DSPCKD_D_PREG_MULT}	D input to P register CLK using multiplier	3.93/ -0.73	4.50/ -0.73	5.35/ -0.73	6.73/ -1.68	ns
T _{DSPDCK_{A,B}_PREG} / T _{DSPCKD_{A,B}_PREG}	A or B input to P register CLK not using multiplier	1.73/ -0.28	1.98/ -0.28	2.35/ -0.28	2.80/ -0.48	ns
T _{DSPDCK_C_PREG} / T _{DSPCKD_C_PREG}	C input to P register CLK not using multiplier	1.54/ -0.26	1.76/ -0.26	2.10/ -0.26	2.54/ -0.45	ns
T _{DSPDCK_PCIN_PREG} / T _{DSPCKD_PCIN_PREG}	PCIN input to P register CLK	1.32/ -0.15	1.51/ -0.15	1.80/ -0.15	2.13/ -0.25	ns
Setup and Hold Times of the CE Pins						
T _{DSPDCK_{CEA;CEB}_{AREG;BREG}} / T _{DSPCKD_{CEA;CEB}_{AREG;BREG}}	{CEA; CEB} input to {A; B} register CLK	0.35/ 0.06	0.42/ 0.08	0.52/ 0.11	0.64/ 0.11	ns
T _{DSPDCK_CEC_CREG} /T _{DSPCKD_CEC_CREG}	CEC input to C register CLK	0.28/ 0.10	0.34/ 0.11	0.42/ 0.13	0.49/ 0.16	ns
T _{DSPDCK_CED_DREG} /T _{DSPCKD_CED_DREG}	CED input to D register CLK	0.36/ -0.03	0.43/ -0.03	0.52/ -0.03	0.68/ 0.14	ns
T _{DSPDCK_CEM_MREG} /T _{DSPCKD_CEM_MREG}	CEM input to M register CLK	0.17/ 0.18	0.21/ 0.20	0.27/ 0.23	0.45/ 0.29	ns
T _{DSPDCK_CEP_PREG} /T _{DSPCKD_CEP_PREG}	CEP input to P register CLK	0.36/ 0.01	0.43/ 0.01	0.53/ 0.01	0.63/ 0.00	ns

Table 28: DSP48E1 Switching Characteristics (Cont'd)

Symbol	Description	Speed Grade				Units
		1.0V		0.9V		
		-3	-2/-2L	-1	-2L	
Setup and Hold Times of the RST Pins						
$T_{DSPDCK_RSTA; RSTB_AREG; BREG}/T_{DSPCKD_RSTA; RSTB_AREG; BREG}$	{RSTA, RSTB} input to {A, B} register CLK	0.41/ 0.11	0.46/ 0.13	0.55/ 0.15	0.63/ 0.40	ns
$T_{DSPDCK_RSTC_CREG}/T_{DSPCKD_RSTC_CREG}$	RSTC input to C register CLK	0.07/ 0.10	0.08/ 0.11	0.09/ 0.12	0.13/ 0.11	ns
$T_{DSPDCK_RSTD_DREG}/T_{DSPCKD_RSTD_DREG}$	RSTD input to D register CLK	0.44/ 0.07	0.50/ 0.08	0.59/ 0.09	0.67/ 0.08	ns
$T_{DSPDCK_RSTM_MREG}/T_{DSPCKD_RSTM_MREG}$	RSTM input to M register CLK	0.21/ 0.22	0.23/ 0.24	0.27/ 0.28	0.28/ 0.35	ns
$T_{DSPDCK_RSTP_PREG}/T_{DSPCKD_RSTP_PREG}$	RSTP input to P register CLK	0.27/ 0.01	0.30/ 0.01	0.35/ 0.01	0.43/ 0.00	ns
Combinatorial Delays from Input Pins to Output Pins						
$T_{DSPDO_A_CARRYOUT_MULT}$	A input to CARRYOUT output using multiplier	3.79	4.35	5.18	6.61	ns
$T_{DSPDO_D_P_MULT}$	D input to P output using multiplier	3.72	4.26	5.07	6.41	ns
$T_{DSPDO_B_P}$	B input to P output not using multiplier	1.53	1.75	2.08	2.48	ns
$T_{DSPDO_C_P}$	C input to P output	1.33	1.53	1.82	2.22	ns
Combinatorial Delays from Input Pins to Cascading Output Pins						
$T_{DSPDO_A; B}_ACOUT; BCOUT}$	{A, B} input to {ACOUT, BCOUT} output	0.55	0.63	0.74	0.87	ns
$T_{DSPDO_A, B}_CARRYCASOUT_MULT}$	{A, B} input to CARRYCASOUT output using multiplier	4.06	4.65	5.54	7.03	ns
$T_{DSPDO_D}_CARRYCASOUT_MULT$	D input to CARRYCASOUT output using multiplier	3.97	4.54	5.40	6.81	ns
$T_{DSPDO_A, B}_CARRYCASOUT$	{A, B} input to CARRYCASOUT output not using multiplier	1.77	2.03	2.41	2.88	ns
$T_{DSPDO_C}_CARRYCASOUT$	C input to CARRYCASOUT output	1.58	1.81	2.15	2.62	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins						
$T_{DSPDO_ACIN_P_MULT}$	ACIN input to P output using multiplier	3.65	4.19	5.00	6.40	ns
$T_{DSPDO_ACIN_P}$	ACIN input to P output not using multiplier	1.37	1.57	1.88	2.44	ns
$T_{DSPDO_ACIN_ACOUT}$	ACIN input to ACOUT output	0.38	0.44	0.53	0.63	ns
$T_{DSPDO_ACIN}_CARRYCASOUT_MULT$	ACIN input to CARRYCASOUT output using multiplier	3.90	4.47	5.33	6.79	ns
$T_{DSPDO_ACIN}_CARRYCASOUT$	ACIN input to CARRYCASOUT output not using multiplier	1.61	1.85	2.21	2.84	ns
$T_{DSPDO_PCIN_P}$	PCIN input to P output	1.11	1.28	1.52	1.82	ns
$T_{DSPDO_PCIN}_CARRYCASOUT$	PCIN input to CARRYCASOUT output	1.36	1.56	1.85	2.21	ns
Clock to Outs from Output Register Clock to Output Pins						
$T_{DSPCKO_P_PREG}$	CLK PREG to P output	0.33	0.37	0.44	0.54	ns
$T_{DSPCKO}_CARRYCASOUT_PREG$	CLK PREG to CARRYCASOUT output	0.52	0.59	0.69	0.84	ns